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## MODEL ANSWER WINTER- 17 EXAMINATION

#### Subject Title: Electronic devices and circuits

**Important Instructions to examiners:** 

Subject Code:

17319

- 1) The answers should be examined by key words and not as word-to-word as given in the model answer scheme.
- 2) The model answer and the answer written by candidate may vary but the examiner may try to assess the understanding level of the candidate.
- 3) The language errors such as grammatical, spelling errors should not be given more Importance (Not applicable for subject English and Communication Skills.
- 4) While assessing figures, examiner may give credit for principal components indicated in the figure. The figures drawn by candidate and model answer may vary. The examiner may give credit for any equivalent figure drawn.
- 5) Credits may be given step wise for numerical problems. In some cases, the assumed constant values may vary and there may be some difference in the candidate's answers and model answer.
- 6) In case of some questions credit may be given by judgement on part of examiner of relevant answer based on candidate's understanding.
- 7) For programming language papers, credit may be given to any other program based on equivalent concept.

Q. No.	Sub Q.N.	Answer	Marking Scheme
Q.1	(A)	Attempt any SIX:	12-Total Marks
	a)	List any two applications of transistor.	2M
	Ans:	Applications of transistor:	Any two 1M each
		<ol> <li>As a switch</li> <li>As an amplifier</li> </ol>	
		3. In Oscillators	
		4. In Multivibrators	
		5. In Time base generators	
	<b>b</b> )	Draw symbol of n-channel and p-channel JFET.	2M
	Ans:	Symbol of n-channel and p-channel JFET:	1M each
		GATE  GATE  GATE  SOURCE  N CHANNEL  P CHANNEL	



• 0	List the types of amplifier			2M	
output of one stage There are mainly the Transformer RC coupling	RC coupling				
		and in oscillator?		2M	
In amplifier negative	ve feedback is used and in os	scillator positive feedback is	sused	1M each	
Compare BJT &	UJT (any two points).			2M	
Sr. No.	ВЈТ	UJT		1M each	
1	Bipolar device	Unipolar device			
2	It has three terminals:	It has three terminals:			
	Emitter, Base, collector	Emitter, Base 1, Base 2			
3	It has two PN junction	It has only PN junction			
List the types of b	iasing of transistor. Which	type of biasing is used mo	estly?	2M	
1. Fixed bias.				1M any tw	
2. Collector-to-ba	se bias.			methods.	
3. Fixed bias with	emitter resistor.				
4. Voltage divider	bias or potential divider.				
_	1				
	er biasing is mostly used.			1M	
		FET.		2M	
Symbol of E-MOS	SFET-			½ M Each	
G GATE	D DRAIN S SOURCE	G D DRAIN S SOURCE P-channel EMOSFET			
	output of one stage There are mainly the Transformer RC coupling Direct coupl Which type of feed In amplifier negative  Compare BJT & Sr. No. 1 2 3 List the types of be 1. Fixed bias. 2. Collector-to-bas. 3. Fixed bias with 4. Voltage divider 5. Emitter bias. The voltage divider 5. Emitter bias. The voltage divider 5. Symbol of E-MOS	output of one stage is connected to the input of There are mainly three types of coupling which  Transformer coupling  RC coupling  Direct coupling  Which type of feedback is used in amplifier as In amplifier negative feedback is used and in ose Compare BJT & UJT (any two points).  Sr. BJT  No.  Bipolar device  It has three terminals: Emitter, Base, collector  It has two PN junction  List the types of biasing of transistor. Which  Fixed bias.  Collector-to-base bias.  Fixed bias with emitter resistor.  Voltage divider bias or potential divider.  Emitter bias.  The voltage divider biasing is mostly used.  Draw neat symbol of E-MOSFET & D-MOS  Symbol of E-MOSFET-	output of one stage is connected to the input of next stage. There are mainly three types of coupling which are  Transformer coupling  RC coupling  Direct coupling  Which type of feedback is used in amplifier and in oscillator?  In amplifier negative feedback is used and in oscillator positive feedback is  Compare BJT & UJT (any two points).  Sr. BJT UJT No.  Bipolar device  It has three terminals: Emitter, Base, collector  Emitter, Base 1, Base 2  It has three terminals: Emitter, Base 1, Base 2  It has only PN junction  List the types of biasing of transistor. Which type of biasing is used mo  1. Fixed bias. 2. Collector-to-base bias. 3. Fixed bias with emitter resistor. 4. Voltage divider bias or potential divider. 5. Emitter bias.  The voltage divider biasing is mostly used.  Draw neat symbol of E-MOSFET & D-MOSFET.  Symbol of E-MOSFET-	output of one stage is connected to the input of next stage. There are mainly three types of coupling which are  • Transformer coupling  • RC coupling  • Direct coupling  • Which type of feedback is used in amplifier and in oscillator?  In amplifier negative feedback is used and in oscillator positive feedback is used  Compare BJT & UJT (any two points).  Sr. BJT UJT No. 1 Bipolar device Unipolar device 2 It has three terminals: Emitter, Base 1, Base 2 3 It has two PN junction It has only PN junction  List the types of biasing of transistor. Which type of biasing is used mostly?  1. Fixed bias. 2. Collector-to-base bias. 3. Fixed bias with emitter resistor. 4. Voltage divider bias or potential divider. 5. Emitter bias. The voltage divider biasing is mostly used.  Draw neat symbol of E-MOSFET & D-MOSFET.  Symbol of E-MOSFET-	

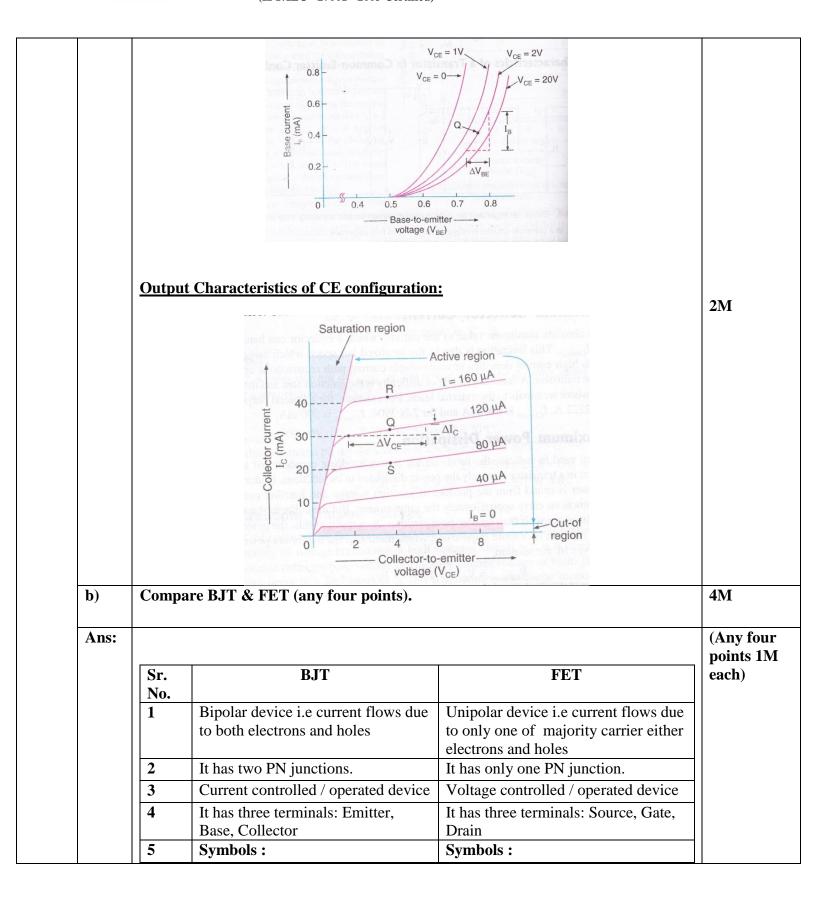


	Symbol of DMOSFE?	Drain(D) Osubstrate	Drain(D)  Sate(G)  Source(S)  P-Channel		½ M Eac
(h)	Write any two applica	ation of tuned ampli	fier.		2M
Ans:	Application of Tuned  1. Communication tra  2. As an RF amplifier	ansmitter and receiver			1M Each
( <b>B</b> )	Attempt any TWO:				8 - Total Marks
a)	Compare CB, CE & (i) Input Resistar (ii) Output Resistar (iii)Current Gain (iv)Voltage gain (	nce (Ri) ance (Ro) (Ai)			4M
Ans:	Parameters	СВ	CE	CC	1M each
	Input Impedance	Low(100Ω)	Low(750Ω)	Very High(750KΩ)	
	Output Impedance	Very High(450KΩ)	$High(45k\Omega)$	$Low(50\Omega)$	
	Current Gain	Less than unity	High (100)	High(100)	
	Voltage Gain  ( Values may didifferent values		very high(about 500)  nt reference books p	Less than 1	
<b>b</b> )	Explain working of U	JT with the help of	VI characteristics.		4M
Ans:	V-I Characteristic :				2M

		Emitter voltage V <sub>E</sub>	
		<ul> <li>Working: <ul> <li>This is graphically representation of emitter voltage versus emitter current. For the emitter potentials less than Vp the UJT is in OFF state.</li> <li>As emitter potential increases and reaches Vp = ηV<sub>BB</sub> + V<sub>D</sub>, the UJT starts conducting. Then with increase in emitter current I<sub>E</sub> the emitter voltage decreases.</li> <li>The reduction in voltage across UJT is due to the drop in resistance R<sub>B1</sub> With increase in value of I<sub>E</sub>.</li> <li>This region is known as "Negative Resistance" region, which is stable enough to be used in various applications.</li> <li>Eventually valley point will be reached and a further increase in I<sub>E</sub> will place the device into saturation.</li> </ul> </li> </ul>	2M
	<b>c</b> )	Draw labelled pin diagram of IC 78 XX and IC 79 XX. Also write the function of these IC's.	4M
	Ans:	Tenction of IC 78 XX and IC 79 XX:-	1M each Pin Diagram ,1M for labeling
		The main function of these IC is to supply required regulated Positive and negative voltage to the electronic circuits.	
Q 2		Attempt any FOUR:	16 – Total Marks
	a)	Draw labelled Input and Output character of transistor in CE configuration.	4M
	Ans:	Input Characteristic of CE configuration:	2M

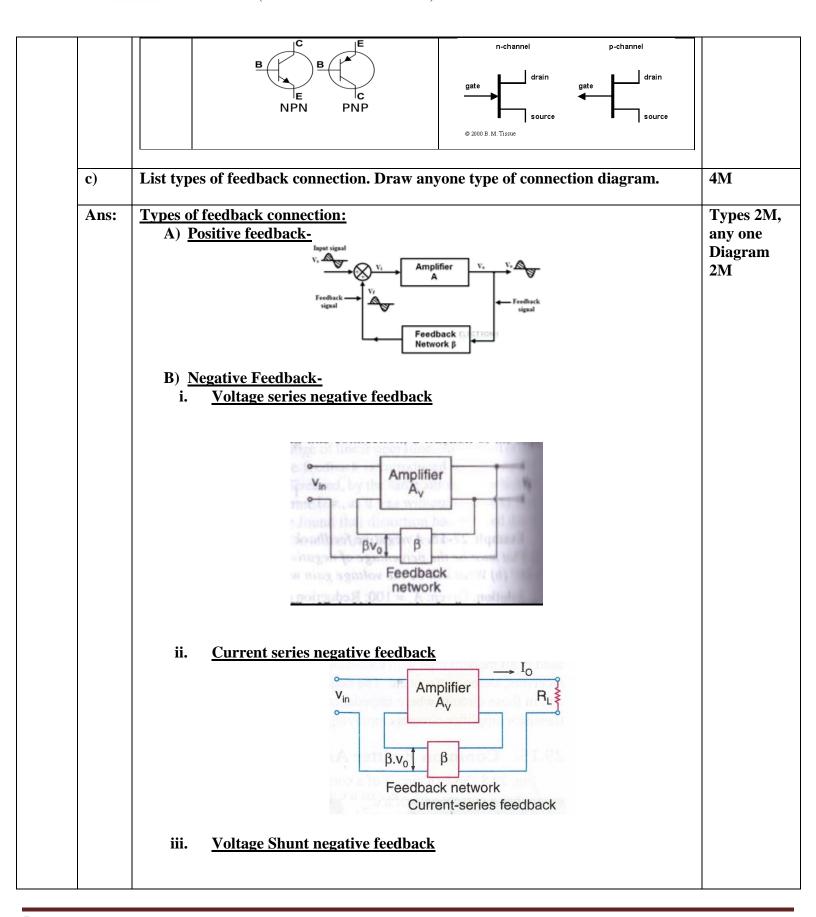


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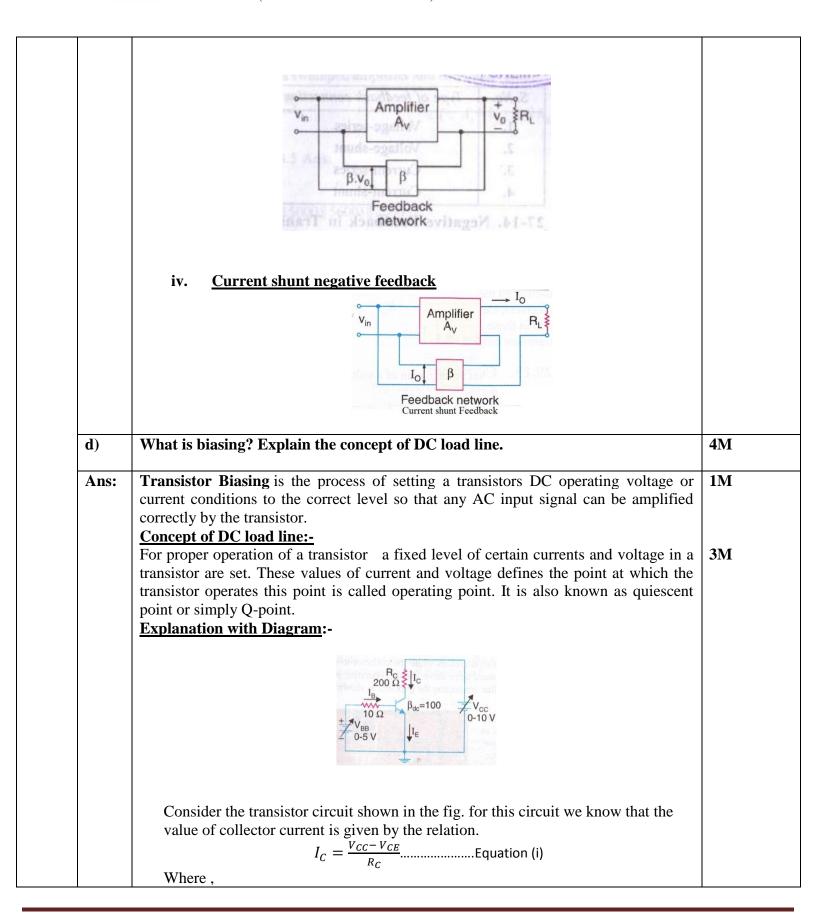


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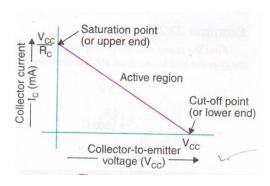
 $V_{CC}$  = value of DC supply voltage in the collector circuit.

 $V_{CE}$  = The value of collector to emitter and

 $R_c$  = value of collector resistance

The value of collector to emitter voltage ( $V_{CE}$ ) at saturation point is very small as compare to  $V_{CC}$  supply. Therefore

$$I_C = \frac{V_{CC}}{R_C}$$



At cut off point the value of collector current is zero substituting  $I_C = 0$  in equation (i)

$$0 = \frac{V_{CC} - V_{CE}}{R_C}$$
OR

 $V_{CE} = V_{CC} = V_{CE(cut off)}$ ....Equation (ii)

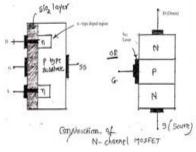
Equation (i),(ii) are the Q point coordinate of DC load line.

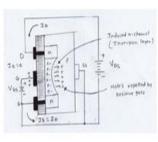
### e) Explain working of E-MOSFET with the help of neat constructional diagram.

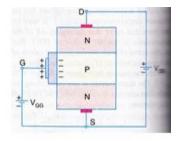
**4M** 

#### Ans:

#### Diagram:







2M

### **Working principle:-**

Case1:- When V<sub>GS</sub>=0 volt

**2M** 

If  $V_{GS}$ =0 volt and a +ve voltage applied between its drain and source, then due to the absence of the n-type channel a zero drain current will result.

<u>Case2:-</u> When V<sub>GS</sub>=positive and V<sub>GS</sub>=positive

	a)	Explain working of transistor as a switch with neat circuit and waveforms.	4M
Q. 3		Attempt any FOUR:	16 – Total Marks
		Remedy to avoid thermal runaway: Thermal runaway can be avoided by 1) Using stabilization circuitry 2) Heat sink	2M
		5. This process becomes cumulative. & amp; it is possible that the ratings of the transistor are exceeded. If it happens, the device gets burnt out. This process is known as 'Thermal Runaway'.	
		<ul><li>3. The increase in power dissipation at collector base junction.</li><li>4. This in turn increases the collector base junction causing the collector current to further increase.</li></ul>	
		<ol> <li>The reverse saturation current in semiconductor devices changes with temperature. The reverse saturation current approximately doubles for every 10<sup>0</sup> c rise in temperature.</li> <li>As the leakage current of transistor increases, collector current (Ic) increases</li> </ol>	
	Ans:	Concept of thermal runaway:	2M
	<b>f</b> )	Describe the concept of thermal runaway. How it can be avoided?	4M
		narrow that means, the channel width will be reduced to a point of pinch off and the saturation condition will occur, hence $I_D$ will remains constant.	
		• The $+V_{GS}$ is kept constant and the $V_{GS}$ is increased gradually .due to this, the gate terminal becomes less and less +ve with respect to drain. So less number of electrons are attracted towards gate terminal and the induced channel becomes	
		<u>Case 3</u> :- Effect of increasing in $V_{DS}$	
		• The electron concentration near $Sio_2$ layer increase to such an extent that it creates an induced n-channel. This connects the n-type doped region. This induced n-channel is called 'inversion layer'. The drain current then start flowing through this induced channel. And the value of $V_{GS}$ at which this conduction begins is called as 'threshold voltage' $V_{GS\ (TH)}$ .	
		<ul> <li>carriers i.e the e-s in the p-type substrate will be attracted towards the gate terminal and gather near the surface of sio<sub>2</sub> layer.</li> <li>As we increase the positive V<sub>GS</sub>, the number of electrons gathers near Sio<sub>2</sub> layer we increase.</li> </ul>	
		<ul> <li>The +ve potential at the gate terminal will repel the holes present in the p-type substrate.</li> <li>This results in creation of a depletion region sio<sub>2</sub> insulting layer. But the minority</li> </ul>	

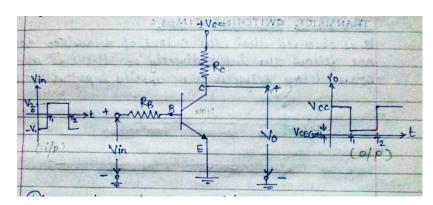


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Ans:

- The switch operates between two states namely saturation and cut-off state.
- The saturation state occurs when both the junctions(i.e. emitter-base junction and collector-base junction) of transistor are forward biased.
- The cut off state occurs when both the junctions of transistors are reverse biased.



(Explanatio

n- 3M)

Figure above shows transistor as a switch with input and output waveforms.

- A input  $(V_{in})$  is applied at the base of the transistor. At time  $T_1$ , the input voltage  $(V_{in})$  is equal to  $\cdot V_1$  and emitter-base junction is reverse biased.  $\cdot$  the transistor is in cut-off and hence practically no current exists in the circuit.
- $: I_B = 0, I_C = \beta. I_B = 0$ Apply KVL to output loop

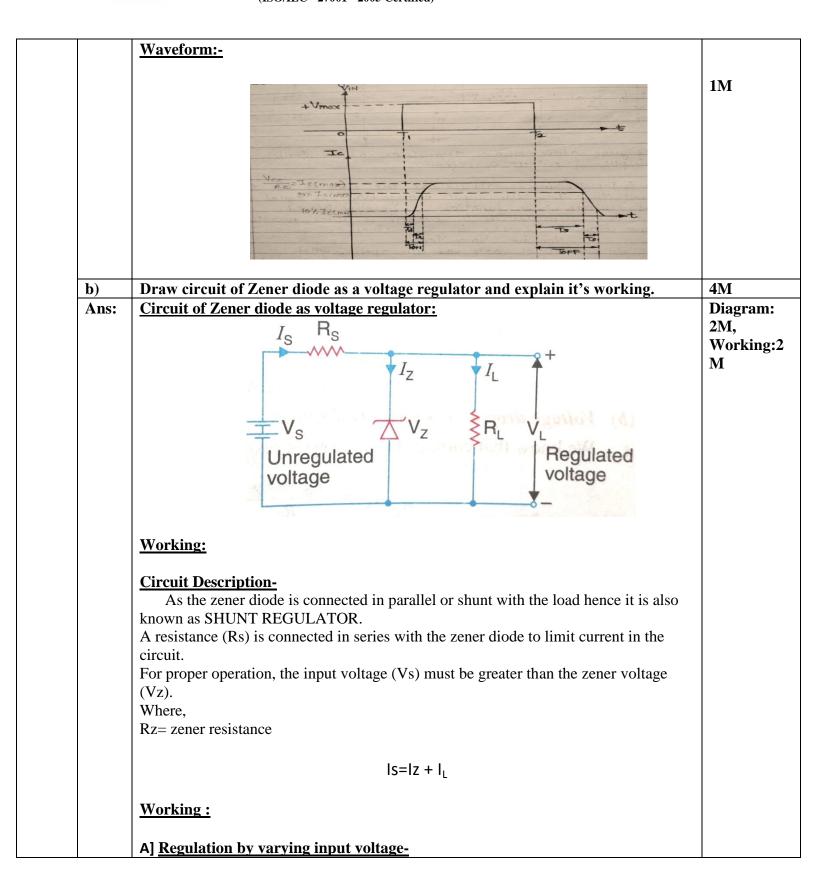
- So transistor acts as an open switch.
- For the time interval  $T_1 < t < T_2$ , the input voltage is equal to  $V_2$ , both the emitter base and collector base junctions are forward biased and the transistor is in saturation.
- The output voltage  $V_0 = V_{CE \text{ (sat)}} = 0.2V$  for silicon and collector current is maximum  $I_C = \frac{V_{CC}}{R_{CC}}$ .
- So transistor acts as a closed switch.
- By applying KVL to output loop:

$$V_{CC} - I_C R_C - V_O = 0$$

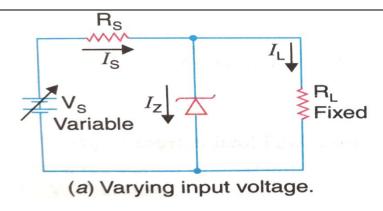
$$V_O = V_{CC} - I_C R_C$$

As I<sub>C</sub> is maximum, I<sub>C</sub>R<sub>C</sub> is also maximum.

 $\therefore$ V<sub>O</sub> is negligible i.e.V<sub>CE(sat)</sub>.



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Here the load Resistance is kept fixed and input voltage is varied within the limits

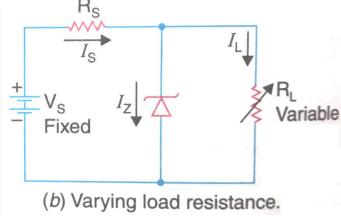
#### **CONDITION 1. -WHEN INPUT VOLTAGE IS INCREASED**

When input voltage is increased the input current (Is) also increases. Thus current through zener diode gets increased without affecting the load current(IL). The increase in input voltage also increases the voltage drop across the resistance Rs thereby keeping the VL constant.

#### **CONDITION 2.- WHEN INPUT VOLTAGE IS DECREASED**

When input voltage is decreased, the input current gets reduced, as a result of this Iz also decreases. The voltage drop across Rs will be reduced and thus the load voltage  $(V_L)$  and load current  $(I_L)$  remains constant.

#### **B] REGULATION BY VARYING LOAD RESISTANCE**



In this method the input voltage is kept constant where as load resistance RL is varied.

#### CONDITION 1. WHEN LOAD RESISTANCE IS INCREASED

When load resistance is increased, the load current reduces, due to which the zener current  $I_Z$  increases. Thus the value of input current and voltage drop across series resistance is kept constant. Hence the load voltage remains constant.



	CONDITION 2. WHEN LOAD RESISTANCE IS REDUCED When load resistance is decreased, the load current increases. This leads to decrease in $I_Z$ . Because of this the input current and the voltage drop across series resistance remains constant. Hence the load voltage is also kept constant.	
<b>c</b> )	List types of FET biasing and explain anyone type with circuit diagram.	4M
Ans:	Types of FET biasing-  i. Self Biasing Method  ii. Voltage Divider bias  iii. Source Bias	List Types:1M, Explain with Circuit diagram
	1. <u>SELF BIASING</u>	3M
	<ul> <li>In this circuit there is only one drain supply and no gate supply.</li> <li>The gate terminal is connected through resistor R<sub>G</sub> to the ground.</li> <li>The source terminal is connected through resistor R<sub>S</sub> to the ground.     {NOTE: In JFET input PN junction between gate &amp; source is always reverse bias, due to this input resistance of JFET is very high. Due to this input gate current I<sub>G</sub> = zero. Hence if resistor R<sub>G</sub> is connected in series with gate terminal, voltage drop across R<sub>G</sub> is zero as V<sub>RG</sub> = I<sub>G</sub> R<sub>G</sub> = 0}     </li> </ul>	
	• $V_G = I_G R_G = 0$ • $V_{GS} = V_G - V_S$ $= -V_S$ APPLY KVL TO INPUT LOOP $V_{GS} + I_D R_S = 0$ $\therefore V_{GS} = -I_D R_S$ • $I_D = I_{DSS} \{1 - \frac{V_{GS}}{V_P}\}^2$ Shockley's equation • APPLY KVL TO OUTPUT LOOP $V_{DD} - I_D R_D - V_{DSQ} - I_D R_S = 0$ $V_{DSQ} = V_{DD} - I_D R_D - I_D R_S$	

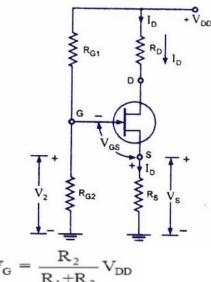
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$$= V_{DD} - I_D [R_D + R_S]$$

### <u>OR</u>

#### 2. VOLTAGE DIVIDER BIAS

The name voltage divider derived from the fact that resistor  $R_1 \& R_2$  are connected on the gate side between the  $V_{\text{DD}}$  supply and ground form a voltage divider.



$$V_G = \frac{R_2}{R_1 + R_2} V_{DD}$$

APPLY KVL TO INPUT LOOP

$$\begin{aligned} V_G - V_{GS} - I_D R_S &= 0 \\ V_{GS} &= V_G - I_D R_S \end{aligned}$$

- $V_{GS} = V_G I_D R_S$   $I_D = I_{DSS} \left\{ 1 \frac{V_{GS}}{V_P} \right\}^2$ Shockley's equation
- APPLY KVL TO OUTPUT LOOP

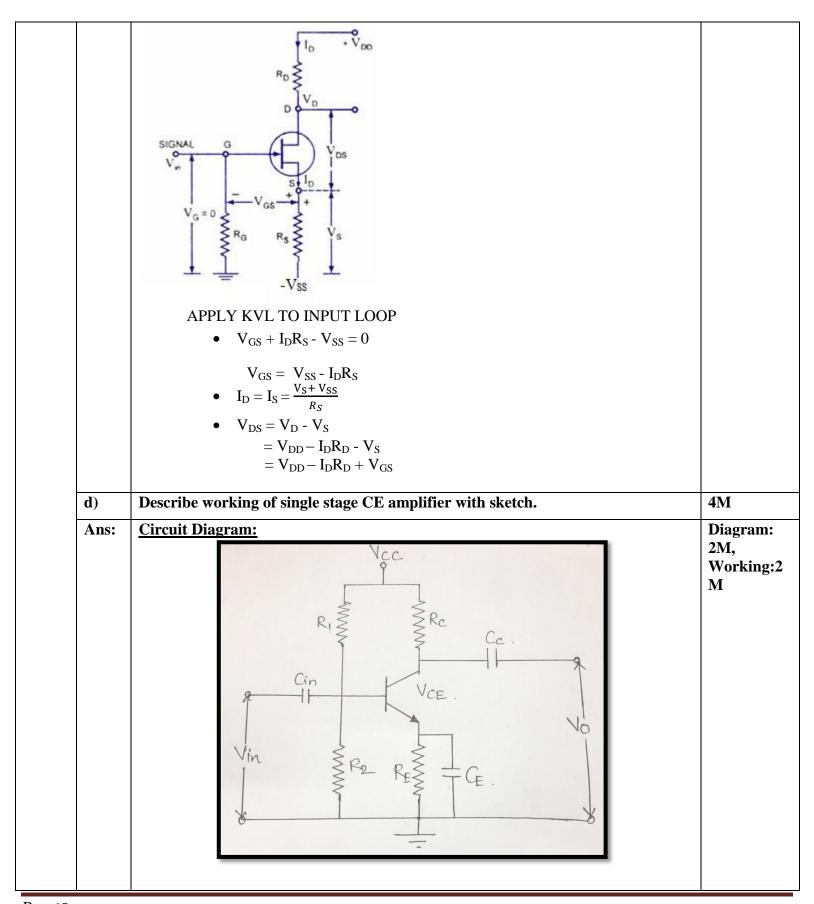
$$\begin{split} V_{DD} - I_D R_D - V_{DSQ} - I_D R_S &= 0 \\ V_{DSQ} &= V_{DD} - I_D R_D - I_D R_S \\ &= V_{DD} - I_D \left[ R_D + R_S \right] \end{split}$$

<u>OR</u>

#### 3. SOURCE BIAS



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#### **Circuit Description:**

- The input a.c. signal is applied across the base emitter terminals of the transistor& output is taken across collector emitter terminals of the transistor.
   V<sub>BB</sub> supply forward biases the emitter base junction & V<sub>CC</sub> supply reverse biases the output junction.
- The Q point is determined by the V<sub>CC</sub> supply along with the resistance R<sub>C</sub>. The resistances R<sub>1</sub>, R<sub>2</sub>, R<sub>E</sub> form the biasing & stabilisation circuit & thus establishes proper operating point.
- Input capacitor  $(C_{in} \approx 10 \mu F)$ : It blocks DC voltage to the base, if it is not provided the source resistance comes across  $R_2$ , so that transistor gets unbiased. It allows a.c. to pass & isolates source resistance from  $R_2$ .
- Emitter capacitance ( $C_E \approx 100 \mu F$ ): it is used in parallel with  $R_E$  to provide a low reactance path to the amplified a.c. signal. If it is not used then amplified a.c. signal flowing through  $R_E$  will cause a voltage drop across it, thus reducing the output voltage.
- Coupling capacitor ( $C_C \approx 10 \mu F$ ): it couples one stage of amplification to the next stage. If it is not used,  $R_C$  comes across with the  $R_1$  of next stage & biasing of  $2^{nd}$  stage gets disturbed. In short it isolates the d.c. of one stage from the next stage but allows the a.c. signal.

#### PHASE REVERSAL / WORKING:

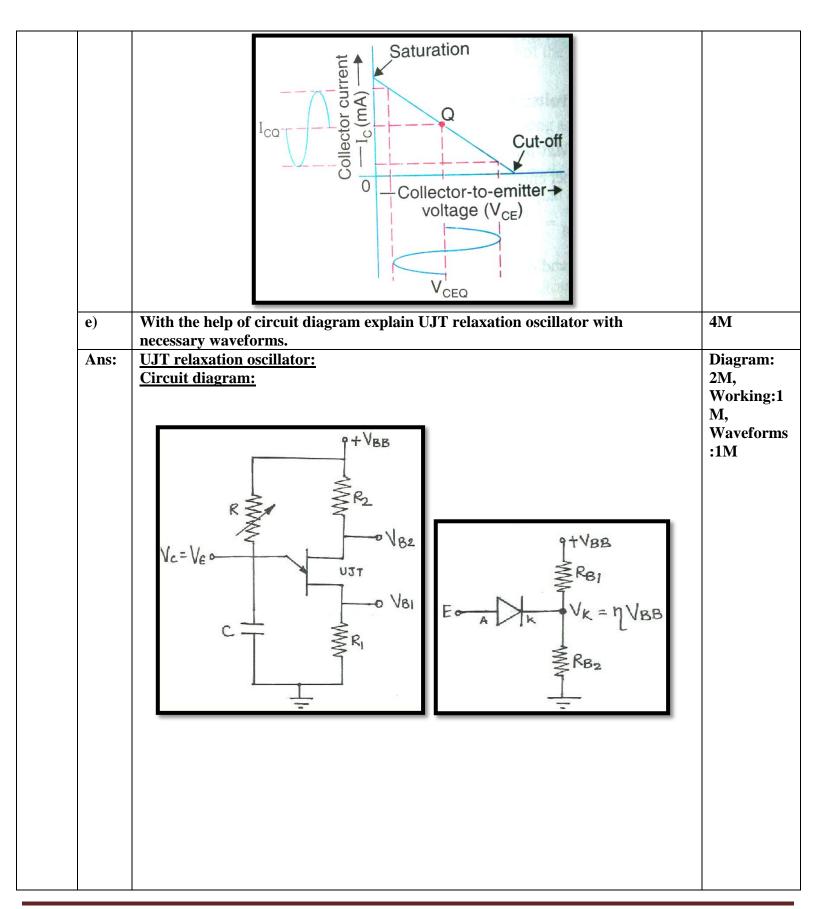
- Consider above common emitter amplifier circuit. The input a.c. signal is applied across the base emitter terminals of the transistor & output is taken across collector emitter terminals of the transistor. VBB supply forward biases the emitter base junction & VCC supply reverse biases the output junction.
- Now apply KVL to collector to emitter loop'

$$VCC - IC RC - VCE = 0.$$
  

$$VCC - IC RC = VCE -----(1)$$

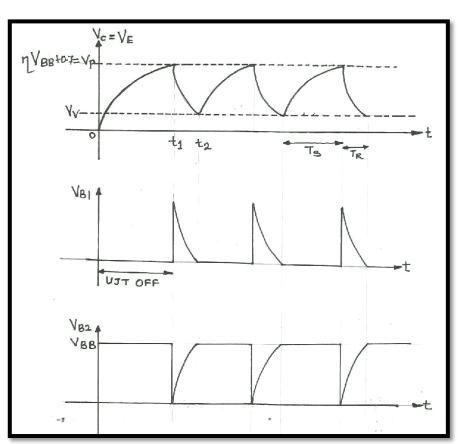
- When the input a.c. signal voltage increases, the base current increases as a result collector current increases (as IC = β I<sub>B</sub>). Hence voltage drop IC RC increases. As VCC is constant, from equation 1 output voltage VCE decreases.
- From above in common emitter amplifier when the input increases in the
  positive, the output voltage decreases. i.e. output is 180° out of phase with
  input.
- Graphically phase reversal is shown as below.

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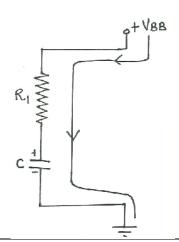




### At t = 0:

- Supply voltage +  $V_{BB}$  is given the circuit then  $V_C = V_E = V_A = 0$  Volts
- By internal potential divider voltage at cathode is
- $\bullet \quad V_K = + \, \eta V_{BB.}$
- If  $V_A(V_E) < V_K$ , then internal PN junction (diode) is reverse biased.
- Therefore, it acts as open switch and UJT is OFF.

### At, t > 0:



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- Current flows from +  $V_{BB}$  to ground through resistor R1 and capacitor C. Thus capacitor starts charging exponentially as constant voltage source +  $V_{BB}$  is applied.
- Hence in waveform from t = 0, and t > 0,  $V_C = V_E$ increasing exponentially.
- Therefore no current flows through UJT.
- $V_{R1} = I.R1 = 0$

 $\mathbf{\dot{\cdot}}V_{B1}=0.$ 

#### At t > 0,

- $\bullet \quad V_{B2} = V_{BB} V_{R2}$
- $\therefore V_{B2} = V_{BB}$  ---- (Since  $V_{R2} = I.R2 = 0$  as I = 0)

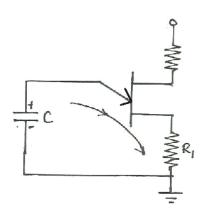
#### At $t = t_1$ :

• Increasing voltage across capacitor is now become  $V_C = (\eta V_{BB} + 0.7)$ Volts. Which is equal to anode voltage from equivalent circuit.

$$\therefore V_C = V_E = V_A = (\eta V_{BB} + 0.7) \text{ Volts.}$$

- As V<sub>A</sub>> V<sub>K</sub> internal PN junction (diode) is forward biased hence it acts as a closed switch, and UJT is ON i.e. UJT starts conducting.
- $V_{B1} = V_{R1} = maximum$  and  $V_{B2} = V_{BB} V_{R2} = 0$

#### At $t > t_1$ :



- Charged capacitor finds path for discharging. Charged capacitor discharges exponentially through ON UJT & resistor R1. i.e. V<sub>c</sub> decreases.
- As  $V_{B1} = V_c$ , therefore  $V_{B1}$  also starts decreasing exponentially.

#### At $t=t_2$ :

- Decreasing capacitor voltage reached to a point where VA = Vk (as VC = VE = VA)
- : Again internal PN junction (diode) reverse biases.
- Therefore UJT is OFF & no current flows through it.
- Therefore all the waveforms continuously repeat themselves.



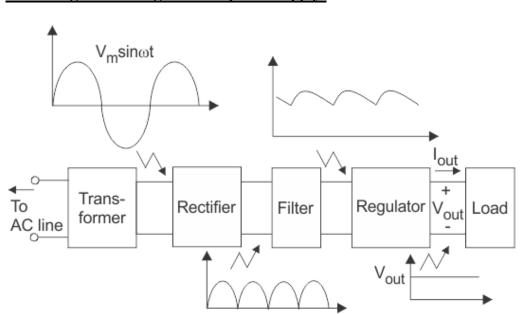
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f) Draw block diagram of DC regulated power supply and explain each block in **4M** detail. Diagram:

2M,

Explain:2M

#### Block diagram of a regulated dc power supply-Ans:



Components of typical linear power supply

- 1. A step down transformer
- 2. A rectifier
- 3. A DC filter
- 4. A regulator

#### **Step Down Transformer**

A step down transformer will step down the voltage from the ac mains to the required voltage level. The turn's ratio of the transformer is so adjusted such as to obtain the required voltage value. The output of the transformer is given as an input to the rectifier circuit.

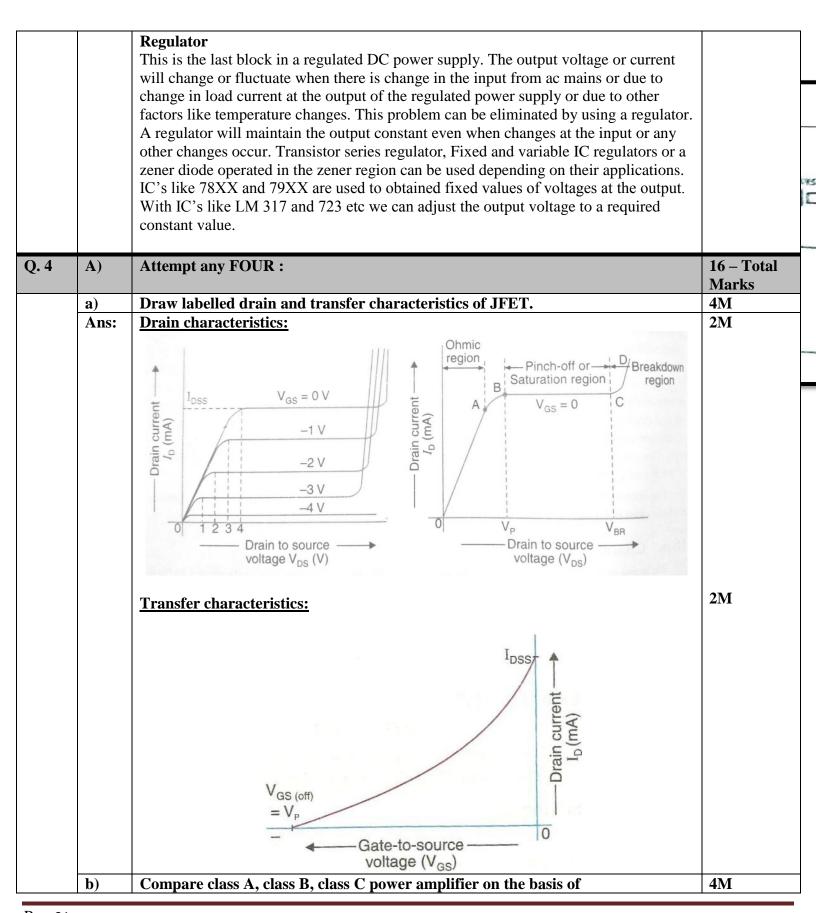
#### Rectification

Rectifier is an electronic circuit consisting of diodes which carries out the rectification process. Rectification is the process of converting an alternating voltage or current into corresponding direct (dc) quantity. The input to a rectifier is ac whereas its output is unidirectional pulsating dc. Usually a full wave rectifier or a bridge rectifier is used to rectify both the half cycles of the ac supply (full wave rectification)

#### **DC** Filter

The rectified voltage from the rectifier is a pulsating dc voltage having very high ripple content. But this is not we want, we want a pure ripple free dc waveform. Hence a filter is used. Different types of filters are used such as capacitor filter, LC filter, Choke input filter,  $\pi$  type filter.

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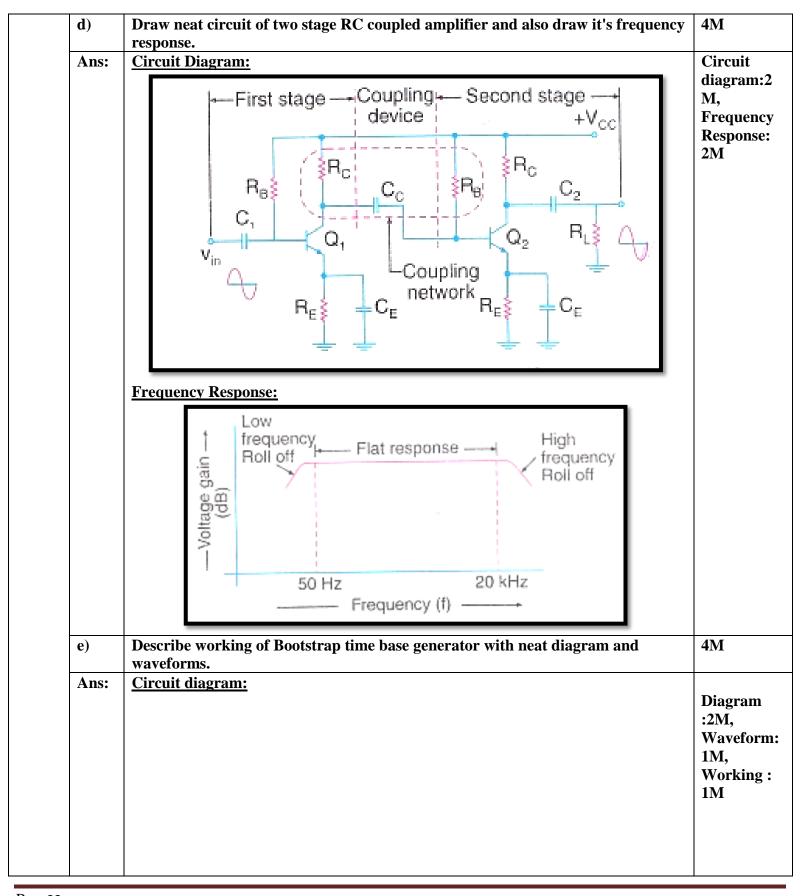




		perating pt. eforms.	(ii) Efficiency (iii) Cond	uction angle (iv) nat	ure of OIP	
Ans:	Sr. No	Parameter	Class A	Class B	Class C	Each poin: 1M
	1	Operating pt.	Centre of DC load line	On the X-axis(in cut –off region)	Below X-axis(below	
	2	Efficiency	Lowest 25% to 50%	Higher (78.5%)	Very high 95%	
	3	Conductio n angle	360 <sup>0</sup> or full cycle	180° or half cycle	Less than $180^{0}$	
	4	Nature of OIP	$i_c$	$i_{c}$ $\int_{\tilde{L}}^{\tilde{L}} \int_{2\pi}^{\pi} 3\pi$	$ic$ $\frac{1}{\pi}$ $\frac{1}{2\pi}$ $\frac{1}{3\pi}$ $\frac{1}{\omega t}$	
c) Ans:			t of crystal oscillator and of Crystal Oscillator:	d give significance of	f piezoelectric effect.	4M Circuit
			RI WANTER C STATE C ST	RFC  C <sub>c</sub> R <sub>L</sub> C <sub>E</sub>	↑ V°	M, Piezoelectr c effect: 2M
	Cryst When vibra	n the crystal i tion depends	property called as piezo-es placed across an ac sour upon the frequency of the	rce, it starts vibrating. e applied voltage ( By	The amount of	

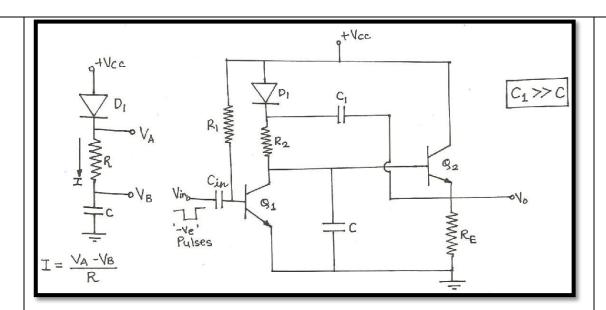


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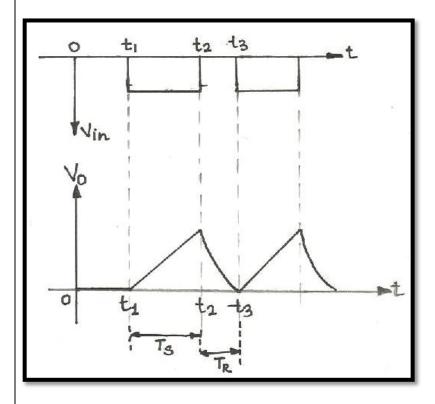




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### **Waveforms:**



### **Working:**

### $\overline{\mathbf{At}\;\mathbf{t}=\mathbf{0}:}$

- Input is not given to the base of transistor  $Q_1$ . Only  $V_{\text{CC}}$  applied.
- Resistor values  $R_1\&\ R_2$  are so selected that  $Q_1$  goes into saturation & acts as a close switch.



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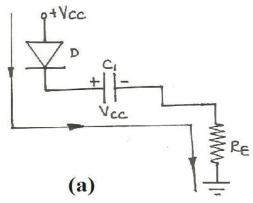
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- Due to this capacitor C is prevented from charging (current flows through Q<sub>1</sub> & goes to ground).
- $:V_{C1} = V_{B2} = 0.2 \text{ V} = V_{CE \text{ (sat)}}$ .
- Therefore transistor Q<sub>2</sub> goes into cut off.
- In the above circuit  $Q_2$  is working as emitter follower & hence output voltage  $V_O$  is taken across resistor  $R_E$ .
- Since  $Q_2$  is off, therefore its emitter current is zero.
- Hence voltage drop across  $R_E$  = output voltage =  $I_E$  \*  $R_E$  = 0 volts. So from t=0 to t<t<sub>1</sub>.

$$Q_1 = ON; V_{C1} = 0.2 V = V_{CE (sat)}$$

$$Q_2 = OFF$$
;  $V_O = V_{RE} = 0$  volts

& current direction in circuit is shown below:



- Now, as shown in above figure (a), C1 charging through resistor (RF + RE) where RF is forward resistance of diode.
- Since both these resistors are small value, charging current is high. ∴C1 charges quickly to +VCCvolts.
- For diode now, VA = VK = +VCC
- Due to this diode is reverse biased & acts as open switch. Hence the above current stops flowing immediately.

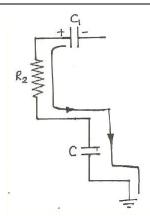
#### At $t = t_1$

• Negative input pulse '-Vin' of sufficient magnitude is given to the base of Q1. Therefore transistor Q1 goes into cutoff & acts as open switch. ∴Capacitor C is now allow to charge through resistor R2. But in this case DC supply voltage used is the charged C1. Which is also equal to +VCC.



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NOTE: Diode D is reverse biased &: acts as open switch. When C starts charging but  $C_1 >> C$ 

- : C<sub>1</sub> does not discharge appreciable]
  - The voltage across capacitor C now starts increasing, which is also a base voltage of  $Q_2$ .
  - Since  $Q_2$  is working as emitter follower, its emitter voltage  $V_{E2} = V_O$  follows base voltage =  $V_C$
  - Hence emitter voltage also starts increasing as capacitor C starts charging.
  - This V<sub>O</sub> is fed back by capacitor C<sub>1</sub> to top point of R<sub>2</sub> (point A) & due to this voltage at point A as well as voltage at point B increases by same amount.
  - Now, voltage drop across  $R_2 = V_A V_B$  remains constant. Due to this charging current through  $R_2$  remains constant.
  - Hence capacitor C charges linearly due to constant current source.
  - Therefore as shown in waveform from  $t = t_1$  to  $t < t_2$  output voltage increases linearly with time.

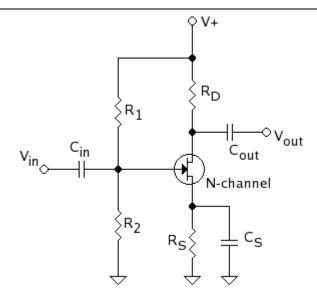
#### At $t = t_2$ to $t = t_3$

- At t = t2 '-Vin' is removed &: Q1 now once again goes into saturation & acts as close switch. The charged capacitor C now quickly discharges through saturation resistor (RSat) of transistor Q1 which is small.
- Hence VO reduces to zero in TR time which is very small. As R2>RSatTs>TR.

f)	Draw and explain common source FET amplifier.	4M
ins:	Circuit Diagram:	Diagram : 2M
		Explanation: 2M

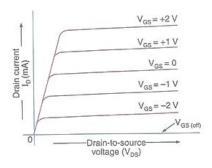
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- Above circuit shows CS N-channel FET amplifier.
- Voltage divider biasing circuit is used.
- C<sub>1</sub> & C<sub>2</sub> are coupling capacitors used to couple input AC signal & output respectively.
- C<sub>S</sub> is a bypass capacitor which keeps the source of FET effectively.

#### **Operation:**



### **DURING POSITIVE HALF CYCLE:**

- As the gate to source voltage increases, the drain current also increases.
- As a result of this, the voltage drop across resistor R<sub>D</sub> also increases.
- This causes the drain voltage to decrease. As  $V_{DS} = V_{DD} I_D R_D$ .
- It means that the positive half cycle of the input produces negative half cycle of the output voltage.
- In other words output voltage is 180° out of phase with the input voltage.

#### **DURING NEGATIVE HALF CYCLE:**

- As the gate to source voltage decreases, the drain current also decreases.
- As a result of this, the voltage drop across resistor R<sub>D</sub> also decreases.
- This causes the drain voltage to increase. As  $V_{DS} = V_{DD} I_D R_D$ .
- It means that the negative half cycle of the input produces positive half cycle of the output voltage.



		Attempt any FOUR:	16 – Total Marks
	a)	Explain operation of NPN transistor with neat constructional diagram.	4M
	Ans:	<u>Diagram :</u>	Diagram : 2M
		N P N I <sub>C</sub> C R <sub>C</sub> Wovement of emitter electrons  Movement of base electrons  B	Explanation: 2M
		<ul> <li>Explanation:</li> <li>The construction for a bipolar NPN transistor is shown above. The voltage between the Base and Emitter (V<sub>BE</sub>), is positive at the Base and negative at the Emitter because for an NPN transistor, the Base terminal is always positive with respect to the Emitter ie. the emitter base junction is forward biased. Also the Collector supply voltage is negative with respect to the Base (V<sub>CB</sub>) ie. collector-base junction is reverse biased.</li> <li>The forward bias on the emitter base junction causes the electrons in the emitter region to flow towards base region. This constitutes I<sub>E</sub>.</li> <li>The electrons after reaching in the base region tend to combine with the holes and they constitute I<sub>B</sub>.</li> <li>However most of the electrons do not combine with the holes in the base region. It is due to the fact that base width is made extremely small and lightly doped and hence electrons do not get sufficient holes for recombination. Thus most of the electrons diffuse to the collector regions and constitute I<sub>C</sub>.</li> <li>The relation between I<sub>E</sub>, I<sub>B</sub> and I<sub>C</sub> is,</li> </ul>	
	<b>b</b> )	Define parameters of JFET  (i) rd (ii) gm (iii) µ and	4M
		Derive relation between them.  Definitions:	Definition
ŀ	Ans:		

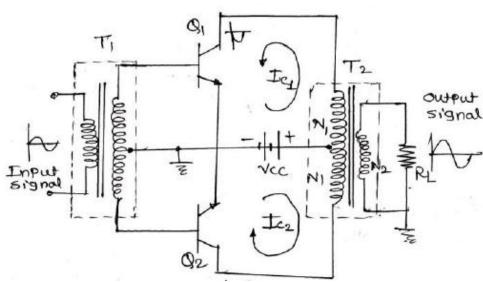


	current for constant gate to source voltage. $rd = \Delta V_{DS}/\Delta I_{D} \text{ keeping constant } V_{GS}$	
	ii) Transconductance (gm): It is defined as ratio of change in drain current ( $\Delta I_D$ ) to the corresponding change in gate to source voltage ( $V_{GS}$ ) at a constant value of drain to source voltage ( $V_{DS}$ )	
	gm = $\Delta I_D/\Delta V_{GS}$ keeping Constant $V_{DS}$	
	iii) Amplification factor ( $\mu$ ) It is defined as the ratio of change in drain to source voltage ( $V_{DS}$ ) to change in the gate to source voltage ( $V_{GS}$ ) at a constant value of $I_D$ .	
	$\mu = \Delta V_{DS} / \Delta V_{GS}$ keeping $I_D$ constant.	
	Relation between μ, gm and rd:	Relation : 1M
	From definitions, $ \mu = \Delta V_{DS} / \Delta V_{GS} \dots i) $ $ gm = \Delta I_D / \Delta V_{GS} \dots ii) $ $ rd = \Delta V_{DS} / \Delta I_D \dots iii) $ $ Multiply and Divide eq i) by \Delta I_D $ $ \mu = (\Delta I_D / \Delta V_{GS}) * (\Delta V_{DS} / \Delta I_D) $ $ i.e \ \mu = gm * rd \ (from ii \& iii) $	
c)	Explain working of class B push pull amplifier with i/p and output waveforms.	4M
Ans:	• In class B amplifier transistor conducts only for half cycle of input signal. This type of output signal gives large distortion. In order to avoid this we use two transistors connected in push-pull arrangement. One conducts in positive half cycle and other conducts in negative half cycle.	Diagram: 1M  Explanatio
	• Transistor T1 is called as input transformer and is called phase splitter and produces two signals which are 180° out of phase with each other. Transistor T2 is called output transformer and is required to couple the a.c. output signal from the collector to the load.	n: 2M Waveforms :1M



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### Class-B Push-Puu Amplifier



#### Working:

- When there is no input signal both the transistor Q1 and Q2 are cut-off. Hence no current is drawn from VCC supply. Thus there is no power wasted in standby the power dissipation in both transistor is practically zero.
- During positive half cycle the base of Q1 is positive and Q2 is negative. As a result of this Q1 conduct, while the transistor Q2 is OFF. And at the output half cycle is obtained.
- During negative half cycle, Q1 turns OFF and Q2 conducts, and another half cycle is obtained at the output. At any instant only one transistor in the circuit is conducting. Each transistor handles one half of the input signal.
- Then output transformer joins these two halves and produces a full-sine wave in the load resistor.

### **Input and output waveforms-**

Input signal



When Q1 conducts



When Q2 conducts





	Ouput signal	
<b>d</b> )	Enlist different types of time base generator. Write any four applications of it.	4M
Ans:	Different types of time base generator: (Any two)	Types: 2M
	1) Voltage time base generator.	
	2) Current time base generator.	
	3) Millers Sweep Generator.	Application
	4) Saw Tooth Generator.	s: 2M (1/2)
	5) Bootstrap Time base generator.	m each for any four)
	Applications of time base generator:	
	1) TV receivers.	
	2) Frequency synthesizer.	
	3) In the electron beam deflection system in cathode ray tube.	
	4) In screen deflection system of a radar.	
e)	Draw and explain transistorized series voltage regulator.	4M
Ans:	Diagram:	2M
	Unregulated voltage  Regulated voltage	
	<ul> <li>Explanation:</li> <li>In this circuit transistor acts as a control element. This transistor is connected in series with the load hence the circuit is called as Series Voltage Regulator. Other components in the circuit are Zener diode (V<sub>Z</sub>), and resistor R.</li> <li>Zener diode V<sub>Z</sub> is operated in breakdown region and provides constant voltage V<sub>Z</sub>.</li> <li>As V<sub>Z</sub> &amp; V<sub>BE</sub> of the transistor are constant, output voltage across R<sub>L</sub> will also be constant. To find output voltage V<sub>O</sub>,</li> </ul>	2M
	Applying KVL to o/p loop of the circuit $V_{BE} + I_L R_L - V_Z = 0$ Therefore, $V_O = I_L R_L = V_Z - V_{BE}$ $V_O = V_Z - V_{BE}$	



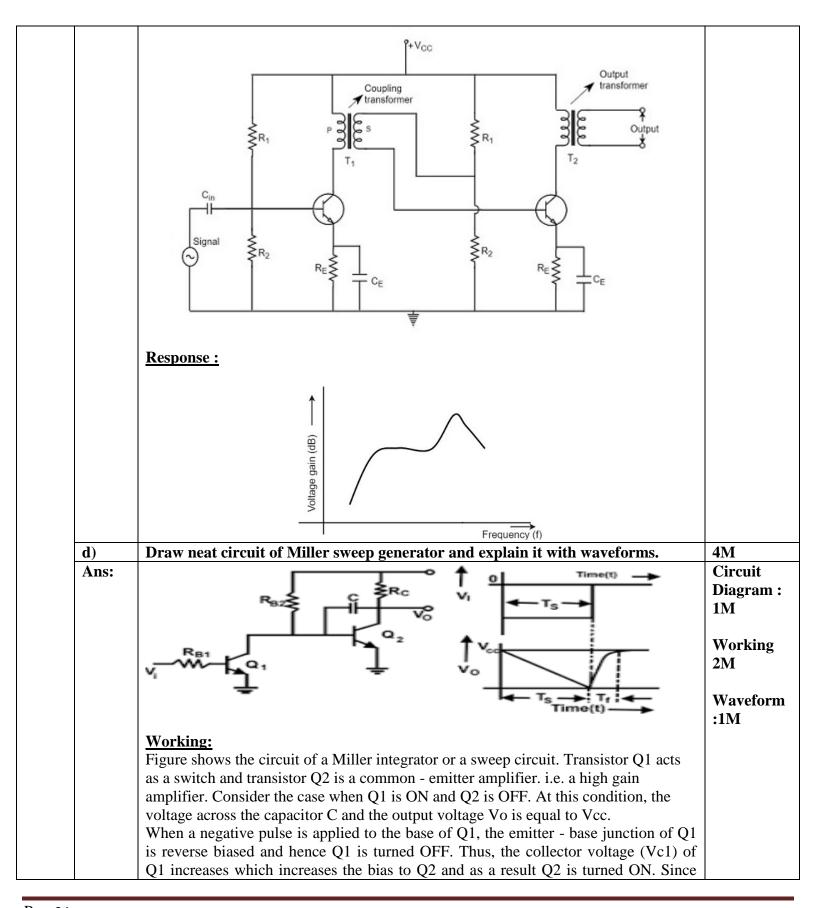
		3) Higher fidelity 4) Less phase distortion 5) Noise reduces	
	Ans:	1) Less amplitude distortion 2) High stabilized gain	Advantage s (any 4): 4M
	a)	List any four advantages of negative feedback.	4M
Q.6		Attempt any FOUR:	16 – Total Marks
		<ul> <li>3) Sensitivity is increased.</li> <li>4) Better Selectivity.</li> <li>Applications of double tuned amplifier:</li> <li>1) Used for coupling the various circuits of radio and television receivers.</li> <li>2) Intermediate frequency (IF) amplifiers in radio receivers.</li> </ul>	Application s: 1M (any two 1/2 m each)
		2) Bandwidth is increased.	two 1/2 m
		Advantages of double tuned amplifier:  1) Better frequency response.	Advantages : 1M (any
		R <sub>1</sub> C <sub>1</sub> L <sub>1</sub> L <sub>2</sub> C <sub>2</sub> Output	
	Ans.	+V <sub>CC</sub>	2111
	f) Ans:	Draw neat circuit diagram of double tuned amplifier. Write any two advantages and two applications of it.  Circuit diagram:	4M 2M
	P	If output voltage increases then $V_{BE}$ decreases. Due to reduction in $V_{BE}$ , $I_{B}$ decreases and $I_{C}$ decreases. This will increase the collector to emitter voltage across the transistor and $V_{O}$ will be regulated this is because $V_{O} = V_{II} - V_{CE}$ If the output voltage decreases, then exactly opposite action will take place and the output voltage is regulated.	



	6) Increased bandwidth	
	7) Less frequency distortion	
<b>b</b> )	Define:	4M
	(i) Load Regulation	
	(ii) Line Regulation	
Ans:	(i) Load Regulation	Definition : 2M each
	The load regulation indicates the change in output voltage that will occur per unit	
	change in load current.	
	Mathematically,	
	$\% \text{ L.R} = \frac{V_{\text{NL}} - V_{\text{FL}}}{100}$	
	$\overline{V_{\mathrm{FL}}}$	
	where,	
	$V_{NL}$ = Load voltage with no load current	
	$V_{FL}$ = Load voltage with full load current	
	(ii) Line Regulation	
	The line regulation or source regulation rating of a voltage regulator indicates the change in output voltage that will occur per unit change in the input voltage.  Mathematically,	
	$\% S.R = \frac{V_{HL} - V_{LL}}{V_{N}} *100$	
	where,	
	V <sub>HL</sub> = Load voltage with high line voltage	
	V <sub>LL</sub> = Load voltage with low load current	
	$V_N$ = output voltage under normal operating conditions	
<b>c</b> )	Draw neat circuit of two stage transformer coupled amplifier and draw it's	4M
	frequency response.	
Ans:	<u>Circuit Diagram :</u>	Circuit Diagram : 2M
		Response : 2M



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Q2 conducts, Vo begins to decrease. Because the capacitor is coupled to the base of transistor Q2, the rate of decrease of output voltage is controlled by rate of discharg	
of capacitor. The time constant of the discharge is given by $td = R_{B2}*C$ .  As the value of time constant is very large, the discharge current practically remain constant. Hence, the run down of the collector voltage is linear. When the input puls	s
is removed, Q1 turns ON and Q2 turns OFF. The capacitor charges quickly to +Vc	
through Rc with the time constant $t = R_C * C$ .	43.4
e) Describe working of RC phase shift oscillator with neat sketch. Write formula for frequency of oscillation.	4M
Ans: $\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Circuit Diagram : 1M
<ul> <li>Working-</li> <li>The circuit consist of a single stage amplifier in C.E configuration and the RC phase shifting network consisting of three identical RC sections.</li> <li>The resistors R<sub>1</sub>, R<sub>2</sub> and R<sub>E</sub> are connected for transistor biasing. C.E is the emitter bypass capacitor.</li> <li>As shown in diagram the output V<sub>O</sub> of single stage C.E amplifier has bee connected as an input to the RC phase shifting network.</li> <li>The output of the phase shifting network is connected at the input of the amplifier.</li> <li>As amplifier is C.E type, it introduces a phase shift of 180° between its input and output. The additional 180° phase shift is introduced by the RC phase shift network.</li> <li>The phase shift around the loop will be precisely equal to 360°. The gain of the amplifier and feedback factor β are adjusted properly to have a loop gain Aβ≥ 1, then sustained sinusoidal oscillations will be obtained at the oscillated output.</li> </ul>	2M  e  ttee  ffn
Frequency of oscillation is given by, $f = \frac{1}{2\pi(\sqrt{6})\text{CR}}$	Formula :1M
f) Draw neat circuit of DC regulated dual power supply for ± 12 V using IC 78 XX	4M



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